TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

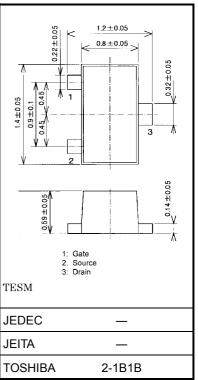
# SSM3K16TE

High Speed Switching Applications Analog Switch Applications

- Suitable for high-density mounting due to compact package
  - Low on resistance:  $R_{on} = 3.0 \Omega (max) (@V_{GS} = 4 V)$ 
    - $: R_{on} = 4.0 \Omega (max) (@V_{GS} = 2.5 V)$
    - $: R_{on} = 15 \Omega (max) (@V_{GS} = 1.5 V)$

# Maximum Ratings (Ta = 25°C)

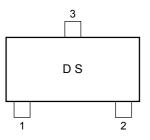
Characteristics		Symbol	Rating	Unit	
Drain-Source voltage		V <sub>DS</sub>	20	V	
Gate-Source voltage		V <sub>GSS</sub>	±10	V	
Drain current	DC	I <sub>D</sub>	100	mA	
	Pulse	I <sub>DP</sub>	200		
Drain power dissipation (Ta = $25^{\circ}$ C)		PD	100	mW	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	

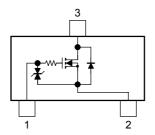


# Marking

# **Equivalent Circuit**







# **Handling Precaution**

When handling individual devices (which are not yet mounting on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

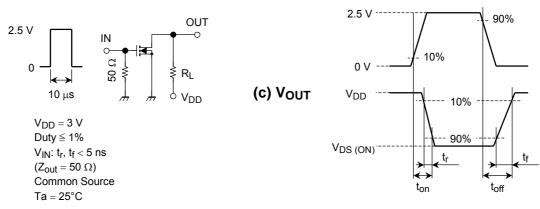
Unit: mm

**Electrical Characteristics (Ta = 25°C)** 

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS}=\pm 10~V,~V_{DS}=0$	_	—	±1	μA
Drain-Source breakdown voltage		V (BR) DSS	$I_D = 0.1 \text{ mA}, V_{GS} = 0$	20			V
Drain cut-off curre	ent	I <sub>DSS</sub>	$V_{DS} = 20 V, V_{GS} = 0$		_	1	μA
Gate threshold vo	ltage	V <sub>th</sub>	$V_{DS} = 3 V, I_D = 0.1 mA$	0.6		1.1	V
Forward transfer a	admittance	Y <sub>fs</sub>	$V_{DS} = 3 V, I_D = 10 mA$	40			mS
Drain-Source ON resistance		R <sub>DS</sub> (ON)	$I_D = 10 \text{ mA}, V_{GS} = 4 \text{ V}$		1.5	3.0	Ω
			$I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$		2.2	4.0	
			$I_D = 1 \text{ mA}, V_{GS} = 1.5 \text{ V}$		5.2	15	
Input capacitance		C <sub>iss</sub>	$V_{DS} = 3 V, V_{GS} = 0, f = 1 MHz$		9.3		pF
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS}=3~V,~V_{GS}=0,~f=1~MHz$		4.5		pF
Output capacitance		C <sub>oss</sub>	$V_{DS} = 3 V$ , $V_{GS} = 0$ , f = 1 MHz	_	9.8		pF
Switching time	Turn-on time	t <sub>on</sub>	$V_{DD} = 3 \text{ V}, \text{ I}_{D} = 10 \text{ mA}, V_{GS} = 0 \sim 2.5 \text{ V}$	_	70		ns
	Turn-off time	t <sub>off</sub>			125		

# **Switching Time Test Circuit**

#### (a) Test circuit



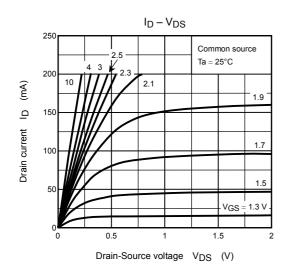
(b) V<sub>IN</sub>

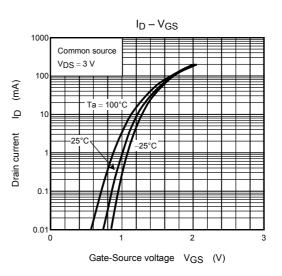
# Precaution

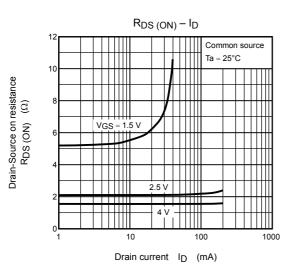
 $V_{th}$  can be expressed as voltage between gate and source when low operating current value is  $I_D = 100 \ \mu A$  for this product. For normal switching operation,  $V_{GS}$  (on) requires higher voltage than  $V_{th}$  and  $V_{GS}$  (off) requires lower voltage than  $V_{th}$ . (Relationship can be established as follows:  $V_{GS}$  (off)  $< V_{th} < V_{GS}$  (on))

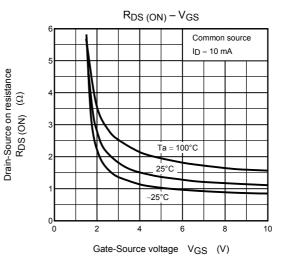
Please take this into consideration for using the device.  $V_{GS}$  recommended voltage of 1.5 V or higher to turn on this product.

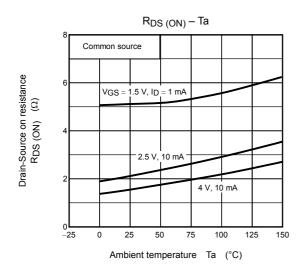
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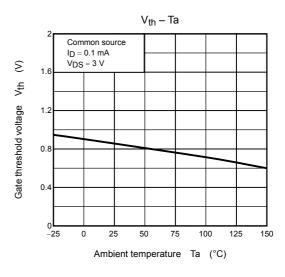




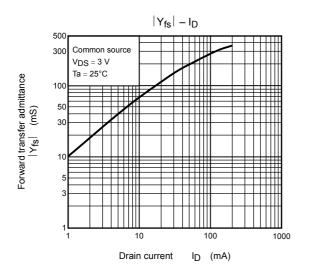


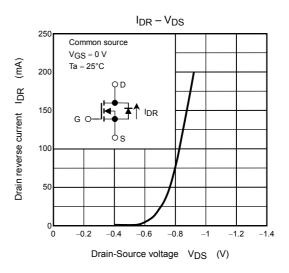


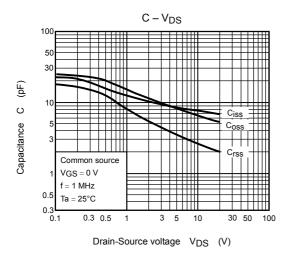


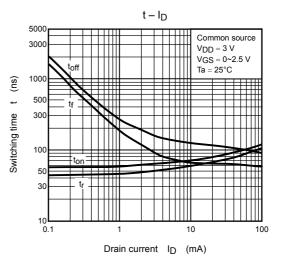


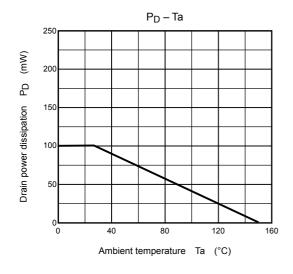
# TOSHIBA











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